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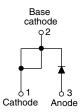
Hyperfast Rectifier, 15 A FRED Pt[®]





TO-220 FULL-PAK

TO-220AC



1

Cathode

VS-15ETX06PbF VS-15ETX06-N3

VS-15ETX06FPPbF VS-15ETX06FP-N3

ბ 3

Anode

PRODUCT SUMMARY								
Package	TO-220AC, TO-220FP							
I _{F(AV)}	15 A							
V _R	600 V							
V _F at I _F	3.2 V							
t _{rr} typ.	18 ns							
T _J max.	175 °C							
Diode variation	Single die							

FEATURES

- Hyperfast recovery time
- Low forward voltage drop
- 175 °C operating junction temperature
- Benchmark ultralow forward voltage drop
- Low leakage current
- Fully isolated package (V_{INS} = 2500 V_{RMS})
- UL E78996 pending
- Compliant to RoHS Directive 2002/95/EC
- Designed and qualified according to JEDEC-JESD47
- Halogen-free according to IEC 61249-2-21 definition (-N3 only)

DESCRIPTION/APPLICATIONS

State of the art hyperfast recovery rectifiers designed with optimized performance of forward voltage drop, hyperfast recovery time, and soft recovery.

The planar structure and the platinum doped life time control guarantee the best overall performance, ruggedness and reliability characteristics.

These devices are intended for use in PFC boost stage in the AC/DC section of SMPS, inverters or as freewheeling diodes.

Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce over dissipation in the switching element and snubbers.

ABSOLUTE MAXIMUM RATINGS									
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS					
Peak repetitive reverse voltage	V _{RRM}		600	V					
Average reatified forward average		T _C = 133 °C	15						
Average rectified forward current	I _{F(AV)}	T _C = 62 °C (FULL-PAK)	15	^					
Non-repetitive peak surge current	I _{FSM}	T _J = 25 °C	170	A					
Peak repetitive forward current	I _{FM}		30						
Operating junction and storage temperatures	T _J , T _{Stg}		- 65 to 175	°C					

ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)										
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS				
Breakdown voltage, blocking voltage	V _{BR} , V _R	I _R = 100 μA	600	-	-					
Forward voltage	V _F	I _F = 15 A - 2.3		2.3	3.2	V				
		I _F = 15 A, T _J = 150 °C	-	1.5	1.8					
	I _R	V _R = V _R rated	-	0.1	50					
Reverse leakage current		$T_J = 150 \text{ °C}, V_R = V_R \text{ rated}$	-	40	300	μA				
Junction capacitance	CT	V _R = 600 V	-	20	-	pF				
Series inductance	L _S	Measured lead to lead 5 mm from package body	-	8.0	-	nH				

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RoHS

COMPLIANT

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DYNAMIC RECOVERY CHARACTERISTICS ($T_C = 25$ °C unless otherwise specified)										
PARAMETER	SYMBOL	TEST CO	NDITIONS	MIN.	TYP.	MAX.	UNITS			
		$I_F = 1 \text{ A}, \text{ d}I_F/\text{d}t = 100$	-	18	22					
Reverse recovery time	+	$I_F = 15 \text{ A}, \text{ d}I_F/\text{d}t = 100$	I _F = 15 A, dI _F /dt = 100 A/μs, V _R = 30 V			32	20			
neverse recovery lime	t _{rr}	T _J = 25 °C		-	22	-	ns			
		T _J = 125 °C	I _F = 15 A dI _F /dt = 200 A/μs V _R = 390 V	-	52	-				
Peak recovery current	I _{RRM}	T _J = 25 °C		-	2.4	-	A			
reak recovery current		T _J = 125 °C		-	5.1	-				
Poverao recovery ebergo	Q _{rr}	T _J = 25 °C		-	25	-	С			
Reverse recovery charge		T _J = 125 °C		-	150	-	C			
Reverse recovery time	t _{rr}		I _F = 15 A dI _F /dt = 800 A/μs	-	37	-	ns			
Peak recovery current	I _{RRM}	T _J = 125 °C		-	16	-	А			
Reverse recovery charge	Q _{rr}		V _R = 390 V	-	350	-	nC			

THERMAL - MECHANICAL SPECIFICATIONS										
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS				
Maximum junction and storage temperature range	T _J , T _{Stg}		- 65	-	175	°C				
Thermal resistance,	P		-	1.0	1.3					
junction to case (FULL-PA	() R _{thJC}		-	3.0	3.5					
Thermal resistance, junction to ambient per leg	R _{thJA}	Typical socket mount	-	-	70	°C/W				
Thermal resistance, case to heatsink	R _{thCS}	Mounting surface, flat, smooth and greased	-	0.5	-					
Weight			-	2.0	-	g				
Weight			-	0.07	-	OZ.				
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)				
Marking davias		Case style TO-220AC	15ETX06							
Marking device		Case style TO-220 FULL-PAK		15ET)	X06FP					

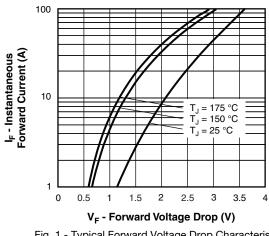
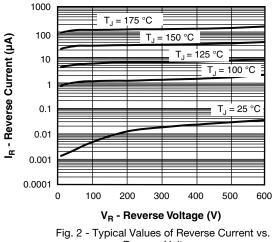


Fig. 1 - Typical Forward Voltage Drop Characteristics



Reverse Voltage

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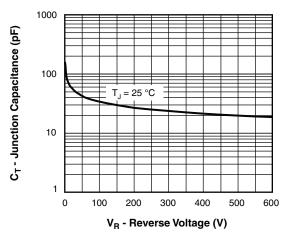


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

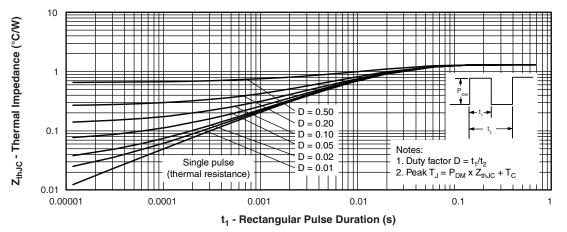


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics

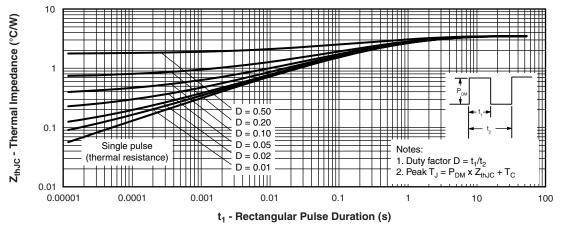
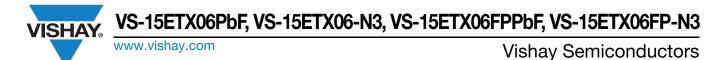


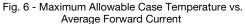
Fig. 5 - Maximum Thermal Impedance Z_{thJC} Characteristics (FULL-PAK)

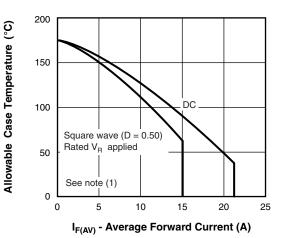
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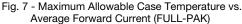


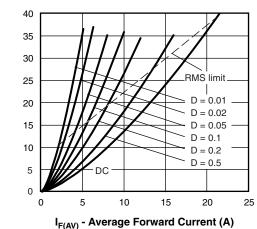
Average Power Loss (W)

180 Allowable Case Temperature (°C) 170 160 150 DC 140 Square wave (D = 0.50)130 Rated V_R applied 120 See note (1) 110 25 5 10 20 0 15 I_{F(AV)} - Average Forward Current (A)



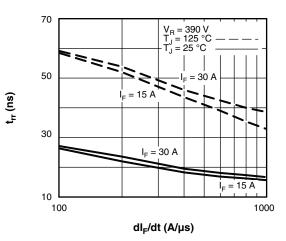






F(AV) - Average i orward ourrent (A)

Fig. 8 - Forward Power Loss Characteristics





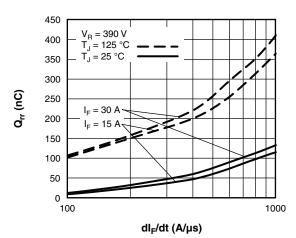


Fig. 10 - Typical Stored Charge vs. dl_F/dt

Note

⁽¹⁾ Formula used: $T_C = T_J - (Pd + Pd_{REV}) \times R_{thJC}$;

Pd = Forward power loss = I_{F(AV)} x V_{FM} at (I_{F(AV)}/D) (see fig. 8); Pd_{REV} = Inverse power loss = V_{R1} x I_R (1 - D); I_R at V_{R1} = Rated V_R

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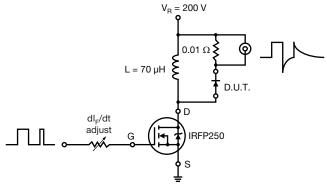
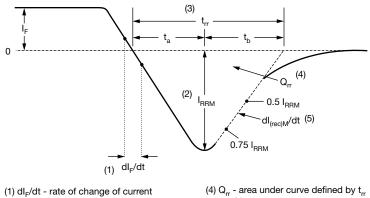


Fig. 11 - Reverse Recovery Parameter Test Circuit



through zero crossing

(2) I_{RRM} - peak reverse recovery current

(3) t_{rr} - reverse recovery time measured from zero crossing point of negative going I_F to point where a line passing through 0.75 I_{RRM} and 0.50 I_{RRM} extrapolated to zero current. (4) Q_{rr} - area under curve defined by t_{rr} and I_{RRM}

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

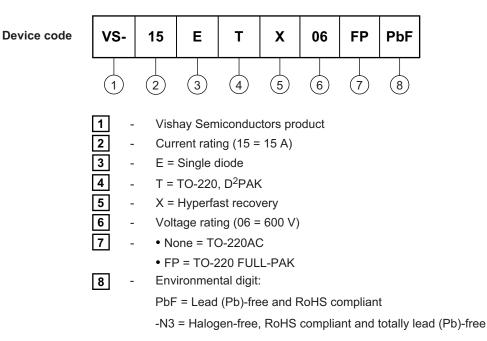
- (5) dI_{(rec)M}/dt peak rate of change of current during $t_{\rm b}$ portion of $t_{\rm rr}$
- Fig. 12 Reverse Recovery Waveform and Definitions

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ORDERING INFORMATION TABLE



ORDERING INFORMATION (Example)										
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION							
VS-15ETX06PbF	50	1000	Antistatic plastic tube							
VS-15ETX06-N3	50	1000	Antistatic plastic tube							
VS-15ETX06FPPbF	50	1000	Antistatic plastic tube							
VS-15ETX06FP-N3	50	1000	Antistatic plastic tube							

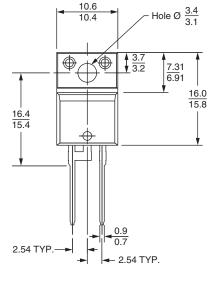
LINKS TO RELATED DOCUMENTS							
Dimensions	TO-220AC	www.vishay.com/doc?95221					
Dimensions	TO-220FP	www.vishay.com/doc?95005					
	TO-220ACPbF	www.vishay.com/doc?95224					
Part marking information	TO-220AC-N3	www.vishay.com/doc?95068					
Part marking information	TO-220AFPPbF	www.vishay.com/doc?95009					
	TO-220FP-N3	www.vishay.com/doc?95440					



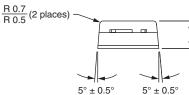
Outline Dimensions

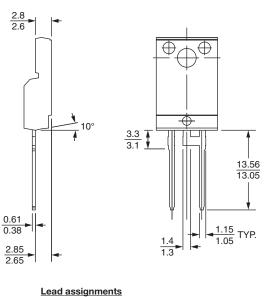
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DIMENSIONS in millimeters



 $\frac{4.8}{4.6}$





<u>Lead assignments</u> <u>Diodes</u> 1 + 2 - Cathode 3 - Anode

Conforms to JEDEC outline TO-220 FULL-PAK



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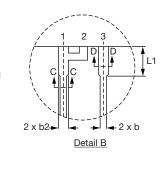
TO-220AC

plane

DIMENSIONS in millimeters and inches









Diodes 1 + 2 - Cathode 3 - Anode

Conforms to JEDEC outline TO-220AC

SYMBOL	MILLIN	IETERS	INCHES		NOTES	SYMBOL	MILLIMETERS		INCHES		NOTES	
STIVIDOL	MIN.	MAX.	MIN.	MAX.	NOTES	STNIBOL	MIN.	MAX.	MIN.	MAX.	NOTES	
А	4.25	4.65	0.167	0.183			E1	6.86	8.89	0.270	0.350	6
A1	1.14	1.40	0.045	0.055			E2	-	0.76	-	0.030	7
A2	2.56	2.92	0.101	0.115			е	2.41	2.67	0.095	0.105	
b	0.69	1.01	0.027	0.040			e1	4.88	5.28	0.192	0.208	
b1	0.38	0.97	0.015	0.038	4		H1	6.09	6.48	0.240	0.255	6, 7
b2	1.20	1.73	0.047	0.068			L	13.52	14.02	0.532	0.552	
b3	1.14	1.73	0.045	0.068	4		L1	3.32	3.82	0.131	0.150	2
с	0.36	0.61	0.014	0.024			L3	1.78	2.13	0.070	0.084	
c1	0.36	0.56	0.014	0.022	4		L4	0.76	1.27	0.030	0.050	2
D	14.85	15.25	0.585	0.600	3		ØР	3.54	3.73	0.139	0.147	
D1	8.38	9.02	0.330	0.355			Q	2.60	3.00	0.102	0.118	
D2	11.68	12.88	0.460	0.507	6		θ	90° t	o 93°	90° t	o 93°	
E	10.11	10.51	0.398	0.414	3, 6							

Notes

⁽¹⁾ Dimensioning and tolerancing as per ASME Y14.5M-1994

- ⁽²⁾ Lead dimension and finish uncontrolled in L1
- (3) Dimension D, D1 and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- ⁽⁴⁾ Dimension b1, b3 and c1 apply to base metal only
- ⁽⁵⁾ Controlling dimension: inches
- ⁽⁶⁾ Thermal pad contour optional within dimensions E, H1, D2 and E1
- ⁽⁷⁾ Dimension E2 x H1 define a zone where stamping and singulation irregularities are allowed
- ⁽⁸⁾ Outline conforms to JEDEC TO-220, D2 (minimum) where dimensions are derived from the actual package outline



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